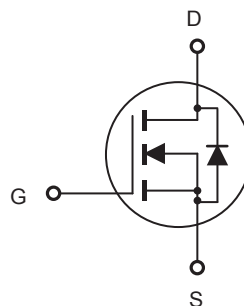
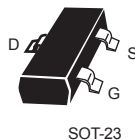


- 30V, 4.8A, $R_{DS(ON)} = 34m\Omega$ @ $V_{GS} = 10V$.
 $R_{DS(ON)} = 40m\Omega$ @ $V_{GS} = 4.5V$.
 $R_{DS(ON)} = 60m\Omega$ @ $V_{GS} = 2.5V$.
- High dense cell design for extremely low $R_{DS(ON)}$.
- Rugged and reliable.
- Lead free product is acquired.
- SOT-23 package.



ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ C$ unless otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	4.8	A
Drain Current-Pulsed ^a	I_{DM}	20	A
Maximum Power Dissipation	P_D	1.25	W
Operating and Store Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Ambient ^b	$R_{\theta JA}$	100	$^\circ C/W$



CES2310

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0V$			1	μA
Gate Body Leakage Current, Forward	I_{GSSF}	$V_{GS} = 12V, V_{DS} = 0V$			100	nA
Gate Body Leakage Current, Reverse	I_{GSSR}	$V_{GS} = -12V, V_{DS} = 0V$			-100	nA
On Characteristics^c						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	0.6		1.4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 4.8A$		28	34	$m\Omega$
		$V_{GS} = 4.5V, I_D = 4A$		32	40	$m\Omega$
		$V_{GS} = 2.5V, I_D = 2A$		45	60	$m\Omega$
Dynamic Characteristics^d						
Forward Transconductance	g_{FS}	$V_{DS} = 10V, I_D = 4.8A$		12		S
Input Capacitance	C_{iss}	$V_{DS} = 15V, V_{GS} = 0V, f = 1.0\text{ MHz}$		610		pF
Output Capacitance	C_{oss}			125		pF
Reverse Transfer Capacitance	C_{rss}			80		pF
Switching Characteristics^d						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15V, I_D = 4.8A, \square$ $V_{GS} = 10V, R_{GEN} = 3\Omega$		10	20	ns
Turn-On Rise Time	t_r			3	6	ns
Turn-Off Delay Time	$t_{d(off)}$			35	70	ns
Turn-Off Fall Time	t_f			4	8	ns
Total Gate Charge	Q_g	$V_{DS} = 15V, I_D = 4.8A, V_{GS} = 4.5V$		9.0	12	nC
Gate-Source Charge	Q_{gs}			2.3		nC
Gate-Drain Charge	Q_{gd}			2.2		nC
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Current ^b	I_S				4.8	A
Drain-Source Diode Forward Voltage ^c	V_{SD}	$V_{GS} = 0V, I_S = 1A$			1	V
Notes : a.Repetitive Rating : Pulse width limited by maximum junction temperature. b.Surface Mounted on FR4 Board, $t < 5$ sec. c.Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$. d.Guaranteed by design, not subject to production testing.						